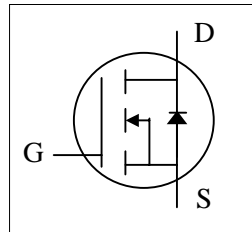




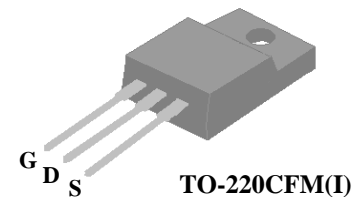
- ▼ Simple Drive Requirement
- ▼ Low On-resistance
- ▼ Fast Switching Characteristic
- ▼ RoHS Compliant



$BV_{DSS}$	30V
$R_{DS(ON)}$	9.5m $\Omega$
$I_D$	62A

### Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.



The TO-220CFM isolation package is widely preferred for commercial-industrial through hole applications.

### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V	62	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS}$ @ 10V	40	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	190	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation	31	W
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

### Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	4.0	$^\circ\text{C}/\text{W}$
Rthj-a	Maximum Thermal Resistance, Junction-ambient	65	$^\circ\text{C}/\text{W}$



# AP72T03GI-HF

## Electrical Characteristics @T<sub>j</sub>=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	-	-	V
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =30A	-	-	9.5	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =15A	-	-	20	mΩ
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	1	-	3	V
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =10V, I <sub>D</sub> =30A	-	37	-	S
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =24V, V <sub>GS</sub> =0V	-	-	10	uA
I <sub>GSS</sub>	Gate-Source Leakage	V <sub>GS</sub> = ±20V, V <sub>DS</sub> =0V	-	-	±100	nA
Q <sub>g</sub>	Total Gate Charge <sup>2</sup>	I <sub>D</sub> =30A	-	15	24	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>DS</sub> =24V	-	3	-	nC
Q <sub>gd</sub>	Gate-Drain ("Miller") Charge	V <sub>GS</sub> =4.5V	-	10	-	nC
t <sub>d(on)</sub>	Turn-on Delay Time <sup>2</sup>	V <sub>DS</sub> =15V	-	8	-	ns
t <sub>r</sub>	Rise Time	I <sub>D</sub> =30A	-	82	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time	R <sub>G</sub> =3.3Ω, V <sub>GS</sub> =10V	-	20	-	ns
t <sub>f</sub>	Fall Time	R <sub>D</sub> =0.5Ω	-	8	-	ns
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> =0V	-	940	1500	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =25V	-	260	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	f=1.0MHz	-	180	-	pF
R <sub>g</sub>	Gate Resistance	f=1.0MHz	-	0.9	1.4	Ω

## Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V <sub>SD</sub>	Forward On Voltage <sup>2</sup>	I <sub>S</sub> =30A, V <sub>GS</sub> =0V	-	-	1.2	V
t <sub>rr</sub>	Reverse Recovery Time <sup>2</sup>	I <sub>S</sub> =10A, V <sub>GS</sub> =0V,	-	28	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI/dt=100A/μs	-	22	-	nC

### Notes:

- 1.Pulse width limited by max. junction temperature.
- 2.Pulse test

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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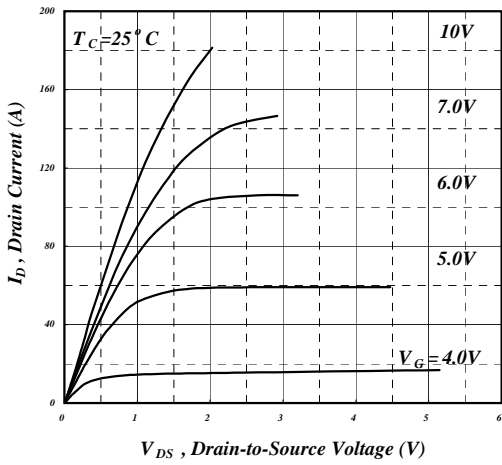


Fig 1. Typical Output Characteristics

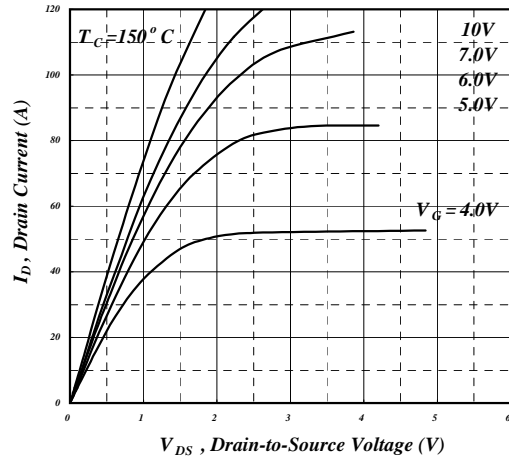


Fig 2. Typical Output Characteristics

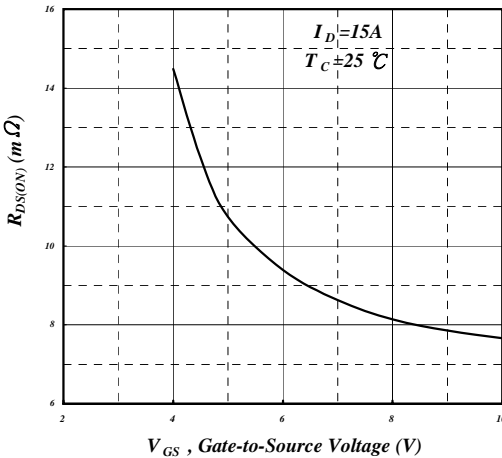


Fig 3. On-Resistance v.s. Gate Voltage

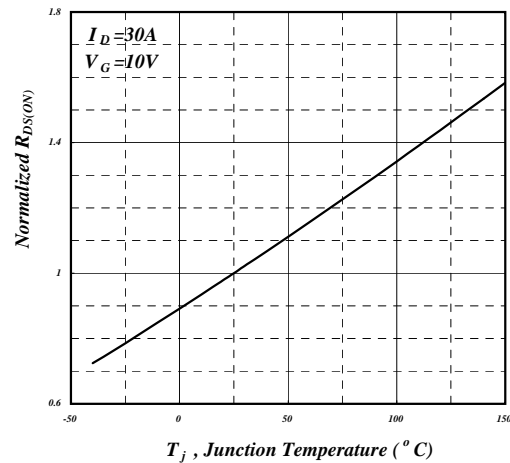


Fig 4. Normalized On-Resistance v.s. Junction Temperature

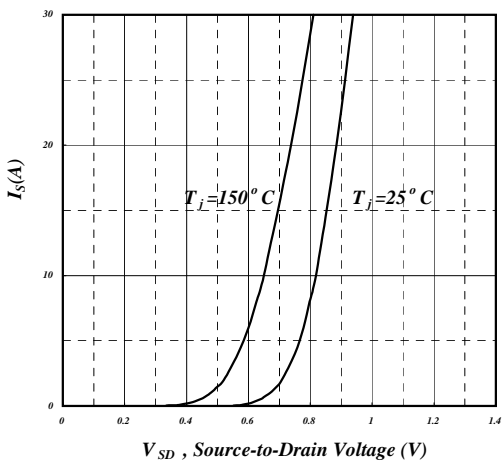


Fig 5. Forward Characteristic of Reverse Diode

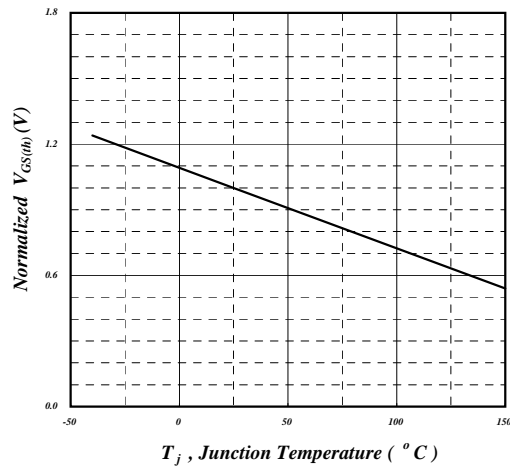


Fig 6. Gate Threshold Voltage v.s. Junction Temperature



# AP72T03GI-HF

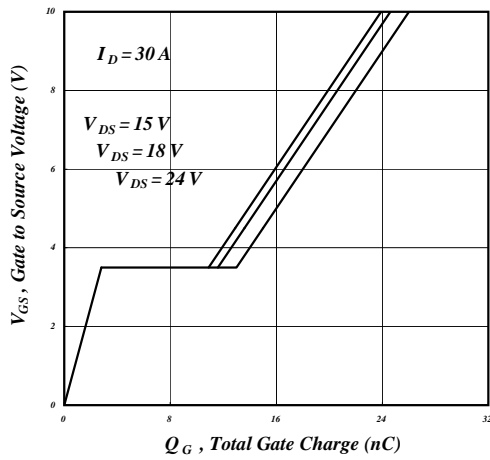


Fig7. Gate Charge Characteristics

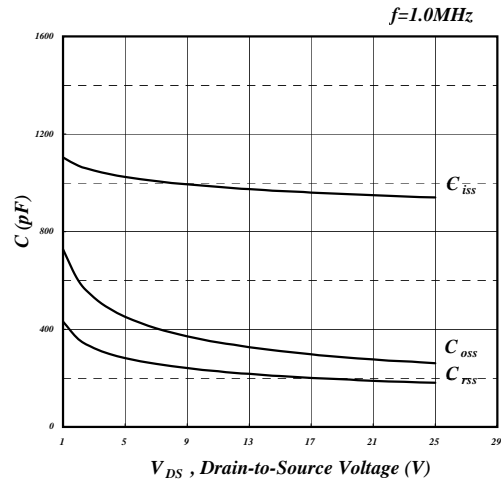


Fig 8. Typical Capacitance Characteristics

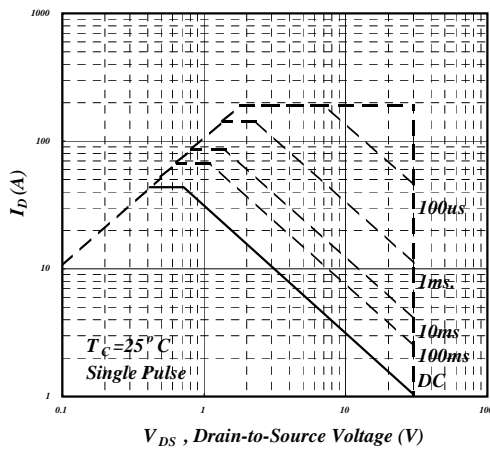


Fig 9. Maximum Safe Operating Area

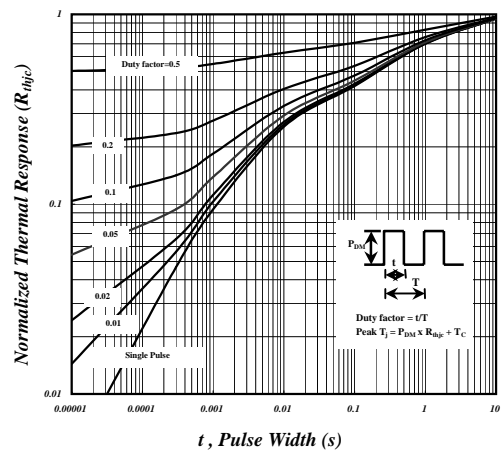


Fig10. Effective Transient Thermal Impedance

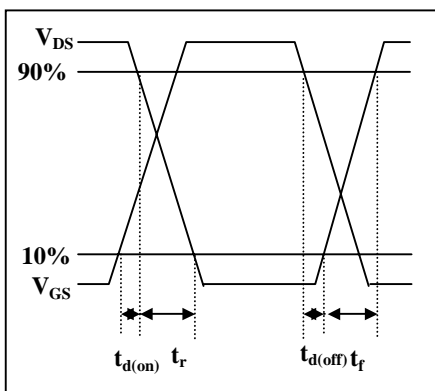


Fig 11. Switching Time Waveform

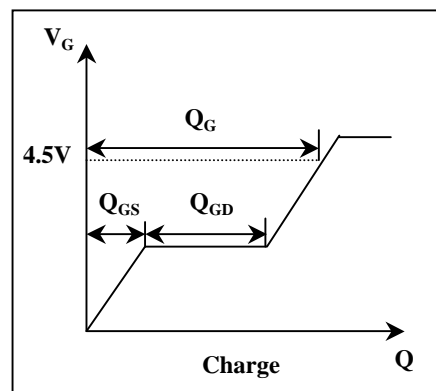


Fig 12. Gate Charge Waveform